

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2810	257/347.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 07:18
L2	0	adhesive with semiconductor with continuous with porous with layer	US-PGPUB	OR	ON	2005/11/28 07:19
S1	2	"6774010"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/14 15:39
S2	11	(adhesive with semiconductor with porous) and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/18 14:41
S3	1	((adhesive with semiconductor with porous) and nm) and MOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/18 14:42
S4	11	(adhesive with semiconductor with porous) and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/18 15:18
S5	1	"6100166" and (high with resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/18 15:20
S6	15	"6100166" and (nitride or high-k)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/18 15:20
S7	103	adhesive with semiconductor with porous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 12:34
S8	236922	(adhesive with semiconductor with porous) and FET or MOS or bipolar	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 12:34

S9	3	(adhesive with semiconductor with porous) and (FET or MOS or bipolar)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/19 12:35
S10	4	(US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did.	US-PGPUB; USPAT	OR	ON	2005/02/14 17:34
S13	2	S10 and monocrystalline	US-PGPUB; USPAT	OR	ON	2005/02/14 17:36
S14	4	S10 and adhesive	US-PGPUB; USPAT	OR	ON	2005/02/14 17:37
S15	4	S10 and (adhesive with substrate)	US-PGPUB; USPAT	OR	ON	2005/02/14 17:38
S16	0	S10 and MOS	US-PGPUB; USPAT	OR	ON	2005/02/14 17:38
S17	2	S10 and transistor	US-PGPUB; USPAT	OR	ON	2005/02/14 17:38
S18	4	(US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did.	US-PGPUB; USPAT	OR	ON	2005/06/07 11:04
S19	4	S18 and porous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:07
S20	4	S19 and adhesive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:07
S21	4	S20 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:08
S22	0	S21 and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:08
S23	0	S21 and MOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:08

S24	1	S21 and FET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:08
S25	4	(US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did.	US-PGPUB; USPAT	OR	ON	2005/06/07 12:44
S26	4	S25 and porous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:44
S27	4	S26 and adhesive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:44
S28	4	S27 and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:44